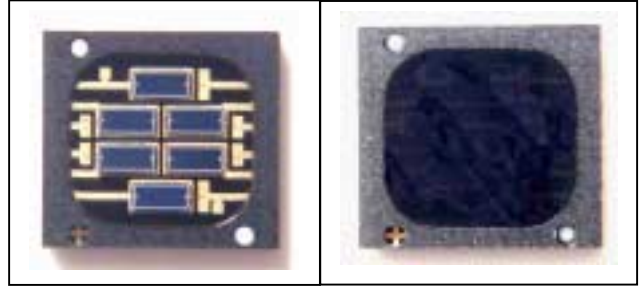


Features of this photodiode array:

- High operating temperature up to 125°C
- Low dark current
- Low capacitance
- High switching speed
- Good uniformity
- Photoconductive or photovoltaic use
- With (OL2100-DF) or without (OL2100) daylight filter

Applications :

Optical encoders, linear or rotary

**Compatible to KOM2100 or OPR2100**

Description	Min.	Typ.	Max.	Unit
Operating and storage temperature, T_a , T_{stg} OL2100-DF	-25		+85	°C
Operating and storage temperature, T_a , T_{stg} OL2100	-55		+125	°C
Reverse breakdown voltage, V_R	50			V
Solder temperature (30sec.), T_{SOL}			235	°C
Sensitivity(S) at $V_R=5V$, $E_e=0.5mW/cm^2$	7	9		μA
Spectral sensitivity (S_λ), no filter	0,53	0,68		A/W
Spectral range OL2100	400		1100	nm
Spectral range OL2100-DF	740		1100	nm
Wavelength of max. sensitivity (λ_{Smax})		950		nm
Active area of each PD chip (A)		2,5		mm ²
Dimension of active area X * Y 1mm x 2,5mm				
Short Circuit Current $E_e = 0,5 mW/cm^2$			8,5	μA
Open Circuit Voltage $E_e = 0,5 mW/cm^2$	250	320		mV
Forward Voltage , $I_F = 10 mA$, $E = 0$		700	750	mV
Reverse Dark Current (I_R), $V_R = 5V$ $T=365K$			150	pA
Rise- / fall time (t_r, t_f), (10%...90%) $R_L = 50\Omega$; $V_R = 20V$, $\lambda=950nm$ $I_p= 800 \mu A$		5		ns
Capacity (C_0) $V_R = 0V$; $f = 1 MHz$; $E = 0$			11	pF
Noise equivalent power (NEP) $T = 300K$; $V_R = 5V$, $\lambda=950nm$		1.5×10^{-14}		W/ $\sqrt{Hz}$

